** <u>*</u>	Application No.	Applicant(s)		
Notice of Allowability	Application No.	Applicant(s)	Applicatings	
	09/854,760	NING, XIAN J.	_	
	Examiner	Art Unit		
	Lan Vinh	1765		
Th MAILING DATE of this communication app All claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate comming GHTS. This application is s	n this application. If not included unication will be mailed in due cour	se. THIS	
1. A This communication is responsive to Amendment filed on 8	<u>3/26/2003</u> .			
2. The allowed claim(s) is/are 1-13 and 22-24.				
3. The drawings filed on 14 May 2002 are accepted by the Ex				
4. ☐ Acknowledgment is made of a claim for foreign priority un a) ☐ All b) ☐ Some* c) ☐ None of the:	der 35 U.S.C. § 119(a)-(d)	or (f).		
<ol> <li>Certified copies of the priority documents have</li> </ol>	been received.			
2. Certified copies of the priority documents have	• •			
<ol><li>Copies of the certified copies of the priority doc</li></ol>	cuments have been received	d in this national stage application t	from the	
International Bureau (PCT Rule 17.2(a)).				
* Certified copies not received:				
5. Acknowledgment is made of a claim for domestic priority ur reference was included in the first sentence of the specifica			pecific	
(a) The translation of the foreign language provisional a	• •			
6. Acknowledgment is made of a claim for domestic priority ur in the first sentence of the specification or in an Application		or 121 since a specific reference wa	as included	
Applicant has THREE MONTHS FROM THE "MAILING DATE" of below. Failure to timely comply will result in ABANDONMENT of the second o	this communication to file a	reply complying with the requirem EE-MONTH PERIOD IS NOT EXT	ents noted ENDABLE.	
7. A SUBSTITUTE OATH OR DECLARATION must be submit INFORMAL PATENT APPLICATION (PTO-152) which give			CE OF	
<ul> <li>8. ☐ CORRECTED DRAWINGS ( as "replacement sheets") mus</li> <li>(a) ☐ including changes required by the Notice of Draftspers</li> <li>1) ☐ hereto or 2) ☐ to Paper No</li> </ul>		v ( PTO-948) attached		
(b) ☐ including changes required by the proposed drawing co	orrection filed whic	h has been approved by the Exami	iner	
(c) ☐ including changes required by the attached Examiner's				
Identifying indicia such as the application number (see 37 CFR 1. each sheet. Replacement sheet(s) should be labeled as such in the	84(c)) should be written on the ne margin according to 37 CF	ne drawings in the front (not the bacl R 1.121(d).	k) of	
9. DEPOSIT OF and/or INFORMATION about the deposit attached Examiner's comment regarding REQUIREMENT FOR TI	sit of BIOLOGICAL MATE HE DEPOSIT OF BIOLOGI	ERIAL must be submitted. Note CAL MATERIAL.	the	
Attachment(s)		`		
1 ☐ Notice of References Cited (PTO-892)	5∐ Notice of Info	ormal Patent Application (PTO-152)	)	
2 Notice of Draftperson's Patent Drawing Review (PTO-948)		mmary (PTO-413), Paper No	_·	
3 Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No	), 7□ Examiner's A	mendment/Comment		
4☐ Examiner's Comment Regarding Requirement for Deposit	8⊠ Examiner's S	Statement of Reasons for Allowance	е	
of Biological Material	9∏ Other			
		Lan Vinh		
		AU 1765		
		$\sim$ ///		

U.S. Patent and Trademark Office PTOL-37 (Rev. 11-03) Application/Control Number: 09/854,760

Art Unit: 1765

## Allowable Subject Matter

1. Claims 1-13, 22-24 are allowed.

The following is an examiner's statement of reasons for allowance:

Regarding claim 1, the cited prior art of record fails to disclose a method for producing a semiconductor device having an alignment mark comprises the step of patterning a second resist layer (the second resist layer is deposited over an etched second dielectric layer) to define a second multiplicity of apertures. The closest cited prior art of Sung et al (US 6,346,454) discloses a method for making dual damascene comprises the step of forming a second resist layer 62 over an etched second dielectric layer 42 and a formed second opening/ aperture 60 without performing a patterning step on the second resist layer to define a second multiplicity of apertures (col 5, lines 65-67; col 6, lines 12-15, fig. 5)

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

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## Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 703 305-6302. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 703 305-2667. The fax phone number for the organization where this application or proceeding is assigned is 703 872-9310.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703 308-0661.

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November 28, 2003

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